

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1.-7 (Cancelled).

8. (Currently Amended) A semiconductor device having a titanium material layer and a silicon oxide layer,

wherein the titanium material layer includes at least one material selected from the group consisting of  $\text{BaTiO}_3$ ,  $\text{SrTiO}_3$ ,  $\text{Ba}_x\text{Sr}_{(1-x)}\text{TiO}_3$ , and similar Group IIA metal titanates, the titanium material layer is provided between an upper electrode and a lower electrode,

~~wherein, when viewed from above the surface of the semiconductor device, the titanium material layer is arranged inside the lower electrode a material for the upper electrode is evaporated on the titanium material layer and lifted off, and~~

~~from a top view, the titanium material layer is longer than the upper electrode.~~

9.-11. (Cancelled).

12. (Currently Amended) The semiconductor device according to claim 8, ~~wherein, when viewed from above the surface of the semiconductor device, the upper electrode is arranged inside the titanium material layer a material for the lower electrode is evaporated on the silicon oxide layer and lifted off, and~~

~~from a top view, the lower electrode is longer than the titanium material layer.~~